



# Complementary 20 V (D-S) Low-Threshold MOSFET

PRODUCT SUMMARY						
	V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)			
		0.280 at V <sub>GS</sub> = 4.5 V	1.28			
N-Channel	20	0.360 at V <sub>GS</sub> = 2.5 V	1.13			
		0.450 at V <sub>GS</sub> = 1.8 V	1			
		0.490 at V <sub>GS</sub> = - 4.5 V	- 1			
P-Channel	- 20	0.750 at V <sub>GS</sub> = - 2.5 V	- 0.81			
		1.10 at V <sub>GS</sub> = - 1.8 V	- 0.67			

#### **FEATURES**

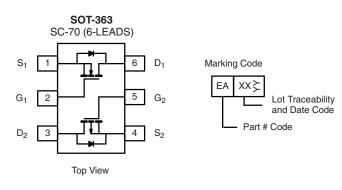
- TrenchFET<sup>®</sup> Power MOSFETS: 1.8 V Rated
- ESD Protected: 2000 V
- Thermally Enhanced SC-70 Package
- Material categorization:
   For definitions of compliance please see www.vishay.com/doc?99912

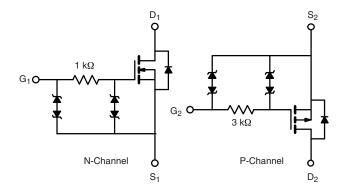


ROHS COMPLIANT HALOGEN FREE

#### **APPLICATIONS**

- Load Switching
- PA Switch
- Level Switch





Ordering Information: Si1563EDH-T1-E3 (Lead (Pb)-free) Si1563EDH-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)								
			N-Channel		P-Channel			
Parameter		Symbol	5 s	Steady State	5 s	Steady State	Unit	
Drain-Source Voltage		$V_{DS}$	20		- 20		V	
Gate-Source Voltage		$V_{GS}$		± 12	± 12		]	
Continuous Drain Current /T 150 °C)	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	1.28	1.13	- 1	- 0.88	1	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 85 °C		0.92	0.81	- 0.72	- 0.63		
Pulsed Drain Current		I <sub>DM</sub>		4 -3		- 3	A	
Continuous Source Current (Diode Conduct	ion) <sup>a</sup>	I <sub>S</sub>	0.61	0.48	- 0.61	- 0.48		
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	0.74	0.57	0.30	0.57	w	
	T <sub>A</sub> = 85 °C		0.38	0.30	0.16	0.3		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150				°C	

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 5 s	R <sub>thJA</sub>	130	170			
Maximum Junction-to-Ambient	Steady State		170	220	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	80	100			

Notes:

a. Surface mounted on 1" x 1" FR4 board.

# Si1563EDH

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SPECIFICATIONS (T <sub>J</sub> = 25 °C	C, unless oth	nerwise noted)						
Parameter				Min.	Тур.	Max.	Unit	
Static	•			,	,			
Gate Threshold Voltage	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	$V_{DS} = V_{GS}, I_D = 100 \mu A$	N-Ch	0.45		1	V	
	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -100 \mu A$	P-Ch	- 0.45		- 1	V	
Gate-Body Leakage		V 0VV .45V	N-Ch			± 1	μΑ	
	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$	P-Ch			± 1		
		V 0VV 10V	N-Ch			± 10	- mA	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	P-Ch			± 10		
		V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V	N-Ch			1	μА	
Zaura Cata Valta va Duniu Comunut		V <sub>DS</sub> = - 16 V, V <sub>GS</sub> = 0 V	P-Ch			- 1		
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C	N-Ch			5		
		V <sub>DS</sub> = - 16 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C	P-Ch			- 5		
On Chata Dunin Command		$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	N-Ch	2			Α	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	P-Ch	- 2				
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 1.13 A	N-Ch		0.220	0.280		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 0.88 A	P-Ch		0.400	0.490		
Durin Course On Otata Basistana a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 0.99 A	N-Ch		0.281	0.360		
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 0.71 A	P-Ch		0.610	0.750	Ω	
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 0.20 A	N-Ch		0.344	0.450		
		V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 0.20 A	P-Ch		0.850	1.10		
Compared Transpoond vistance <sup>3</sup>	_	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.13 A	N-Ch		2.6		S	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 0.88 A	P-Ch		1.5			
Diada Farriard Valtagra	.,,	I <sub>S</sub> = 0.48 V, V <sub>GS</sub> = 0 V	N-Ch		0.8	1.2	V	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = - 0.48 V, V <sub>GS</sub> = 0 V	P-Ch		- 0.8	- 1.2		
Dynamic <sup>b</sup>			<u> </u>			<u> </u>		
Total Cata Charma			N-Ch		0.65	1		
Total Gate Charge	$Q_g$	N-Channel	P-Ch		1.2	1.8	nC	
Oata Carras Charras	$Q_{gs}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 1.13 \text{ A}$	N-Ch		0.2			
Gate-Source Charge		P-Channel	P-Ch		0.3			
Octo Davis Observe	Q <sub>gd</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 0.88 A	N-Ch		0.23			
Gate-Drain Charge			P-Ch		0.3			
Turn On Delay Time	t <sub>d(on)</sub>		N-Ch		45	70		
Turn-On Delay Time		N-Channel	P-Ch		150	230	ns	
Rise Time	t <sub>r</sub>	$V_{DD} = 10 \text{ V}, R_L = 20 \Omega$	N-Ch		85	130		
		$I_D \cong 0.5 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 6 \Omega$	P-Ch		480	720		
Turn Off Dolou Tim-	t <sub>d(off)</sub>	P-Channel	N-Ch		350	530		
Turn-Off Delay Time		$V_{DD}$ = - 10 V, $R_L$ = 20 $\Omega$	P-Ch		840	1200		
Call Time	t <sub>f</sub>	$I_D \cong$ - 0.5 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 6 $\Omega$	N-Ch		210	320		
Fall Time			P-Ch		850	1200		

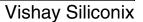
#### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 

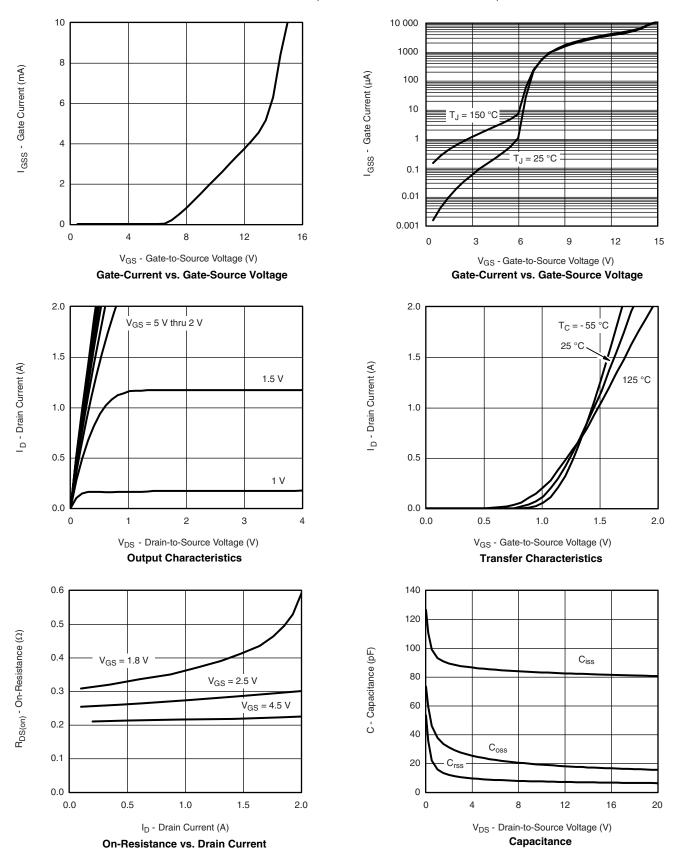
b. Guaranteed by design, not subject to production testing.







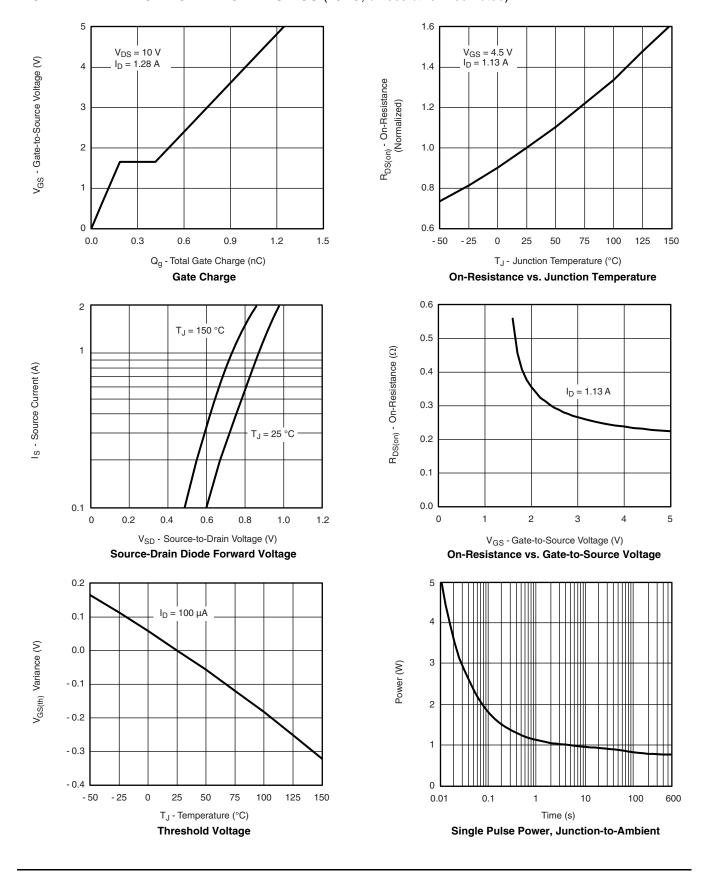
#### N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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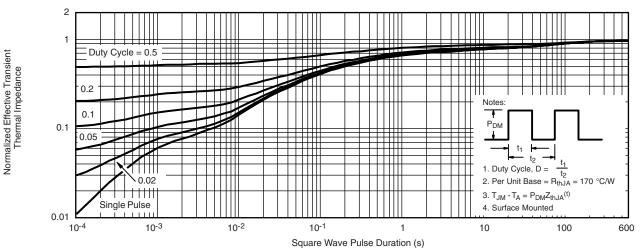
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## N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

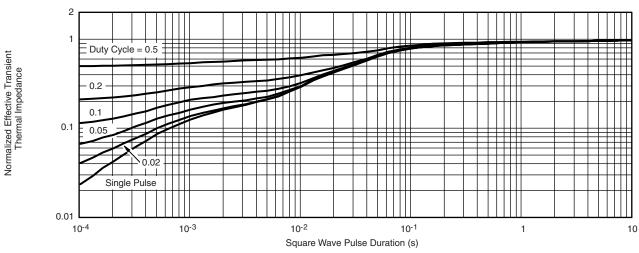




## N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

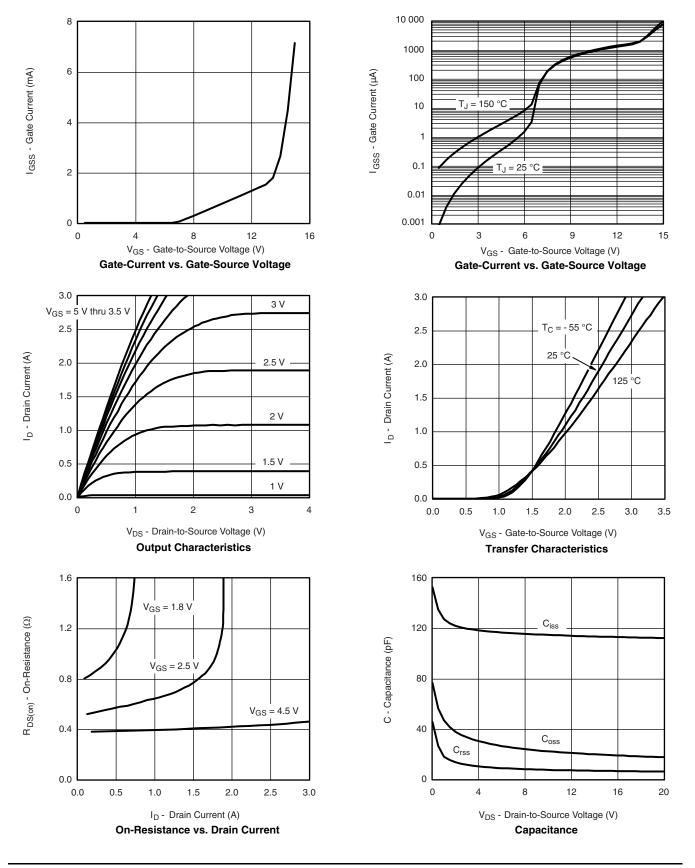


Normalized Thermal Transient Impedance, Junction-to-Foot

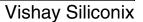
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## P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

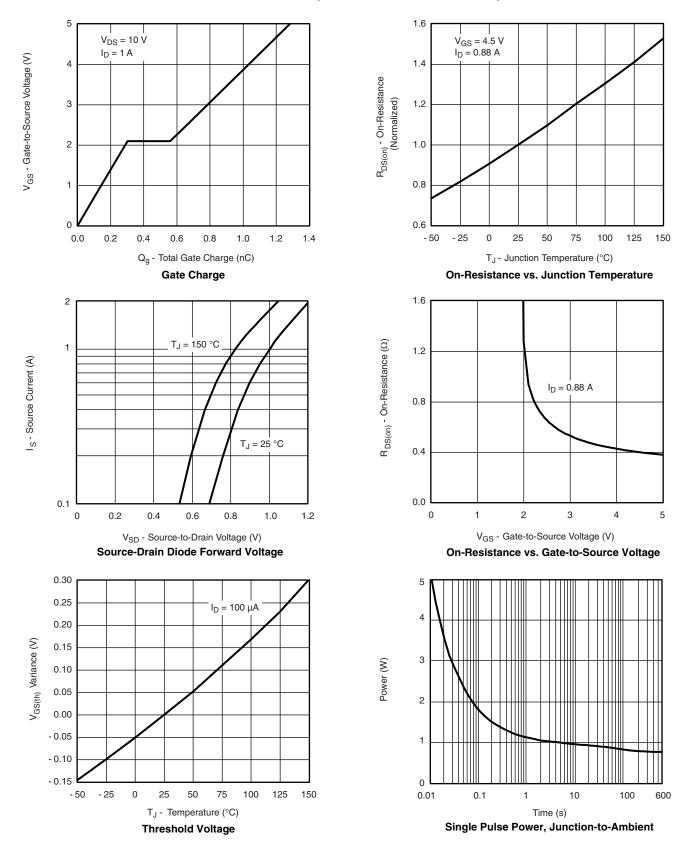








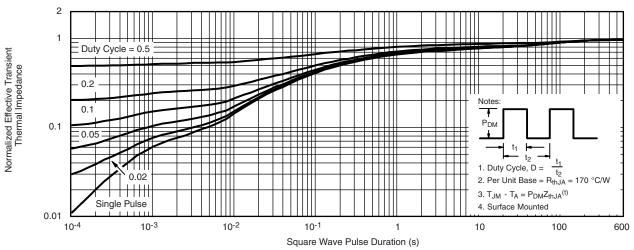
#### P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



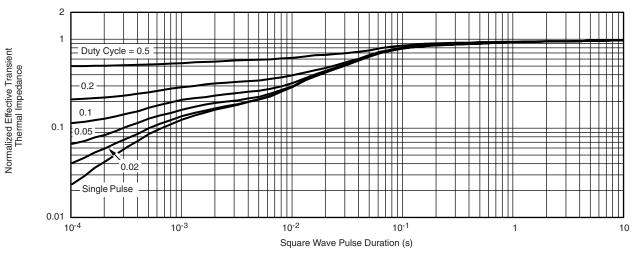
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#### P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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